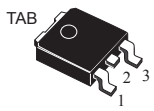
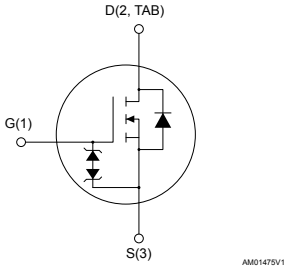
N-channel 600 V, 320 mΩ typ., 10 A, MDmesh M6 Power MOSFET in a DPAK package



DPAK



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}
STD13N60M6	600 V	380 mΩ	10 A	92 W

- Reduced switching losses
- Lower $R_{DS(on)}$ per area vs previous generation
- Low gate input resistance
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications
- LLC converters
- Boost PFC converters

Description

The new MDmesh M6 technology incorporates the most recent advancements to the well-known and consolidated MDmesh family of SJ MOSFETs. STMicroelectronics builds on the previous generation of MDmesh devices through its new M6 technology, which combines excellent $R_{DS(on)}$ per area improvement with one of the most effective switching behaviors available, as well as a user-friendly experience for maximum end-application efficiency.

STPOWER

Product status link
STD13N60M6

Product summary	
Order code	STD13N60M6
Marking	13N60M6
Package	DPAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_{case} = 25 °C	10	A
	Drain current (continuous) at T_{case} = 100 °C	6.4	
I_{DM}(1)	Drain current (pulsed)	28	A
P_{TOT}	Total power dissipation at T_{case} = 25 °C	92	W
I_{AR}(2)	Avalanche current, repetitive or not repetitive	2	A
E_{AS}(3)	Single pulse avalanche energy	140	mJ
dv/dt(4)	Peak diode recovery voltage slope	15	V/ns
dv/dt(5)	MOSFET dv/dt ruggedness	100	
T_{stg}	Storage temperature range	-55 to 150	°C
T_j	Operating junction temperature range		

1. *Pulse width is limited by safe operating area.*
2. *Pulse width limited by T_{jmax}.*
3. *Starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V.*
4. *I_{SD} ≤ 10 A, di/dt = 400 A/µs, $V_{DS(peak)}$ < $V_{(BR)DSS}$, V_{DD} = 400 V*
5. *V_{DS} ≤ 480 V*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	1.36	°C/W
$R_{thj\text{-}pcb}$(1)	Thermal resistance junction-pcb	50	

1. *When mounted on an 1-inch² FR-4, 2 Oz copper board.*

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V			1	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_{case} = 125 °C (1)			100	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3.25	4	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 5 A		320	380	mΩ

1. *Defined by design, not subject to production test.*

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	509	-	pF
C_{oss}	Output capacitance		-	34.4	-	
C_{rss}	Reverse transfer capacitance		-	4.2	-	
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	94	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	5.6	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 10 A, V_{GS} = 0 to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	13	-	nC
Q_{gs}	Gate-source charge		-	3.4	-	
Q_{gd}	Gate-drain charge		-	6.4	-	

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 5 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	15.8	-	ns
t_r	Rise time		-	6.5	-	
$t_{d(off)}$	Turn-off delay time		-	25.5	-	
t_f	Fall time		-	9.4	-	

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		10	A
I_{SDM} (1)	Source-drain current (pulsed)		-		28	A
V_{SD} (2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 10 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 10 A, di/dt = 100 A/µs, V_{DD} = 60 V (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	182		ns
Q_{rr}	Reverse recovery charge		-	1.35		µC
I_{RRM}	Reverse recovery current		-	14.8		A
t_{rr}	Reverse recovery time	I_{SD} = 10 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	253		ns
Q_{rr}	Reverse recovery charge		-	2		µC
I_{RRM}	Reverse recovery current		-	16		A

1. *Pulse width is limited by safe operating area.*
2. *Pulse test: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

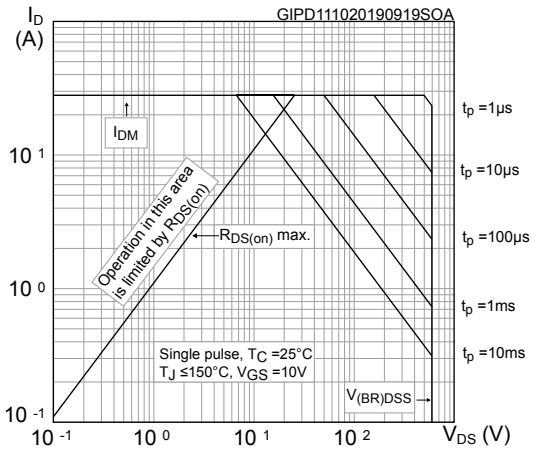


Figure 2. Maximum transient thermal impedance

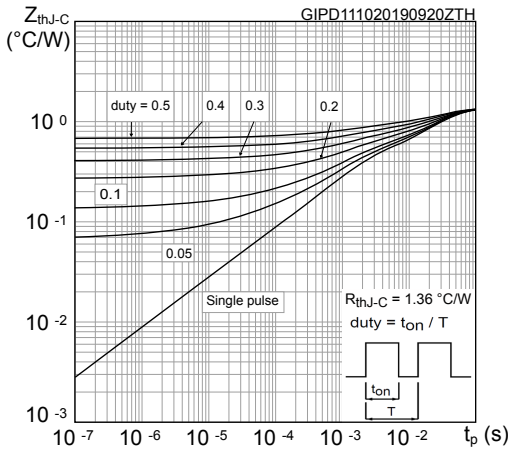


Figure 3. Typical output characteristics

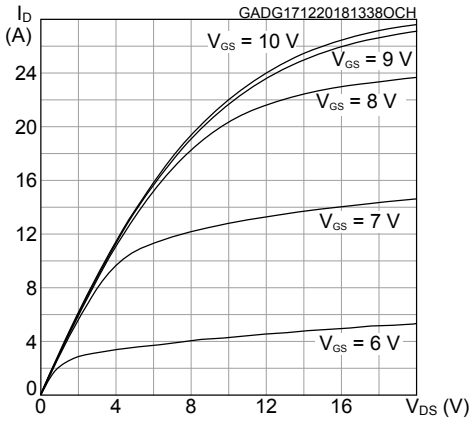


Figure 4. Typical transfer characteristics

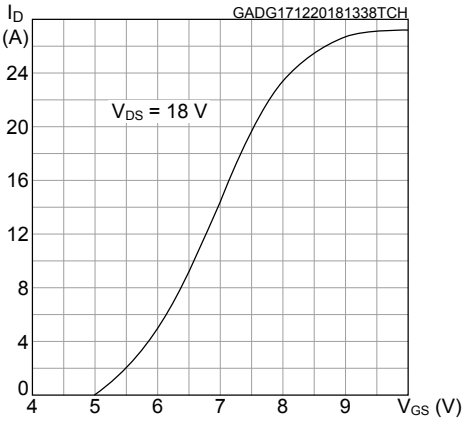


Figure 5. Typical gate charge characteristics

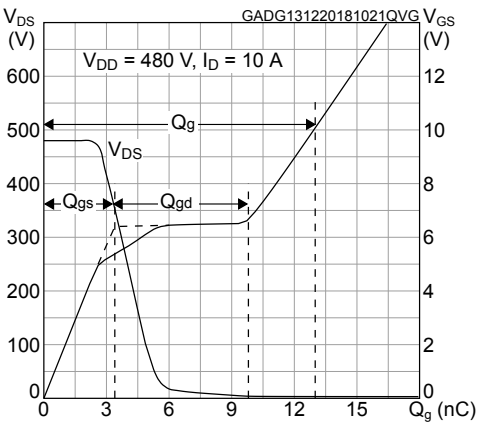


Figure 6. Typical drain-source on-resistance

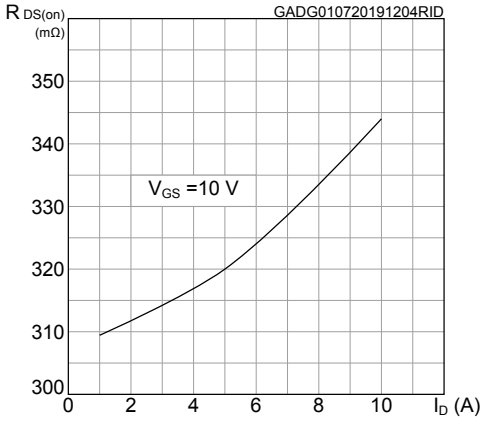


Figure 7. Typical capacitance characteristics

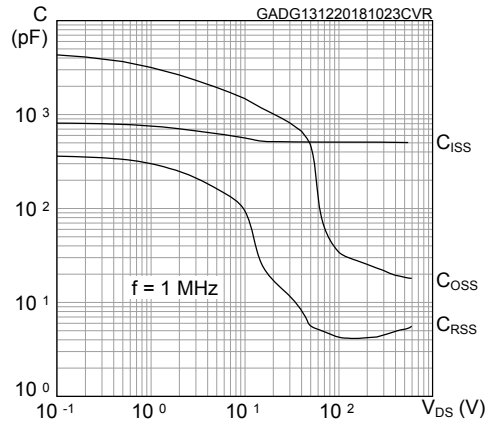


Figure 8. Typical output capacitance stored energy

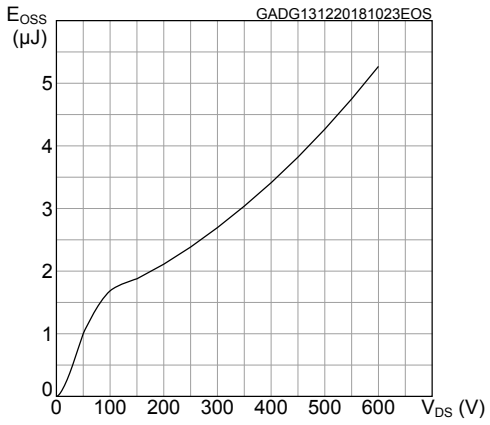


Figure 9. Normalized gate threshold vs temperature

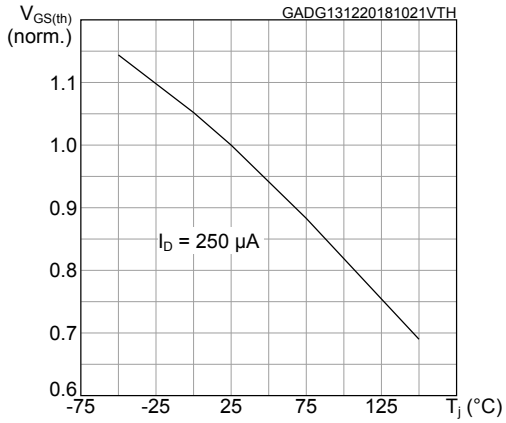


Figure 10. Normalized on-resistance vs temperature

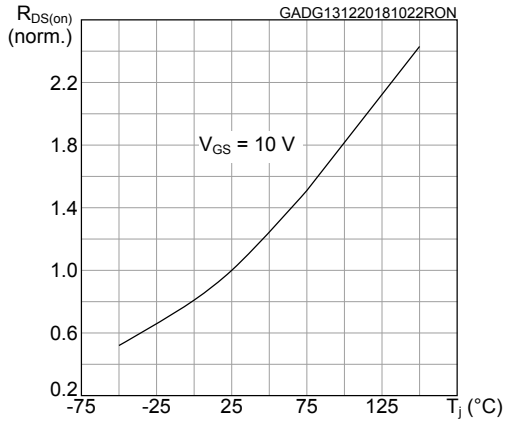


Figure 11. Normalized breakdown voltage vs temperature

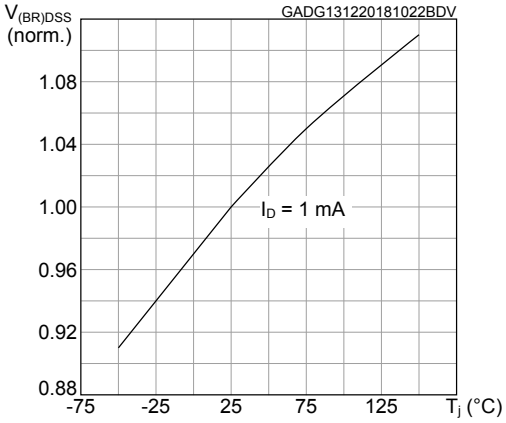
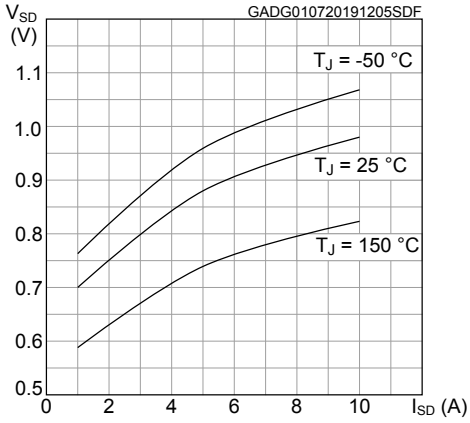


Figure 12. Typical reverse diode forward characteristics



3 Test circuits

Figure 13. Test circuit for resistive load switching times

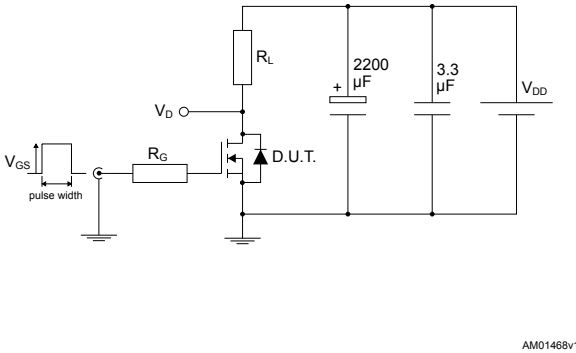


Figure 14. Test circuit for gate charge behavior

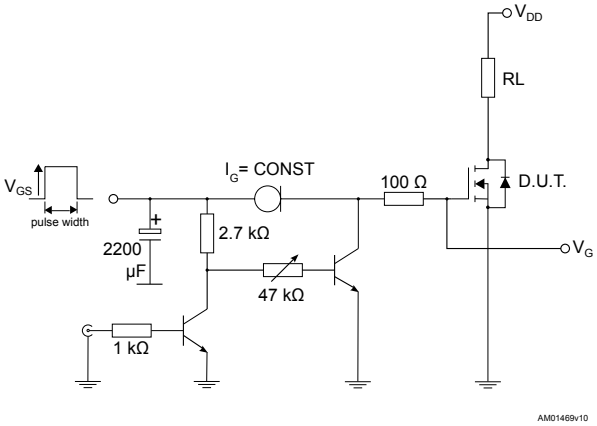


Figure 15. Test circuit for inductive load switching and diode recovery times

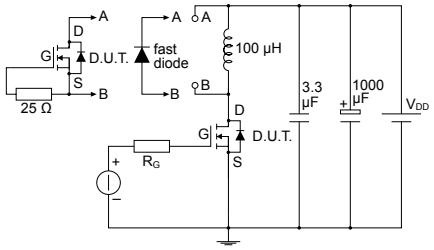


Figure 16. Unclamped inductive load test circuit

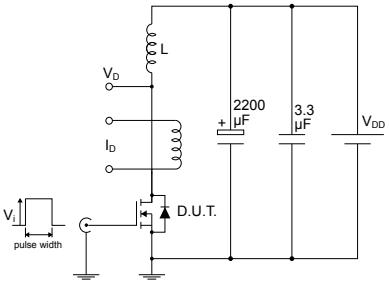


Figure 17. Unclamped inductive waveform

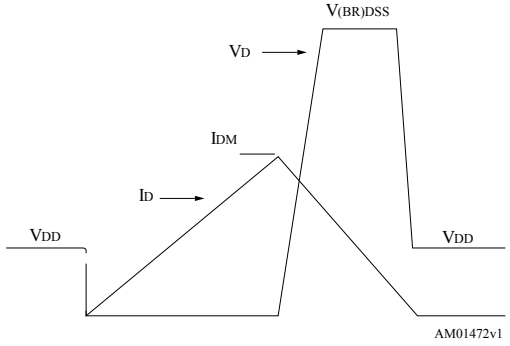
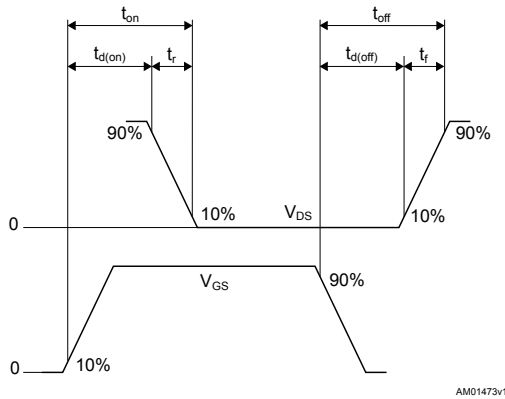


Figure 18. Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 DPAK (TO-252) type A2 package information

Figure 19. **DPAK (TO-252) type A2 package outline**

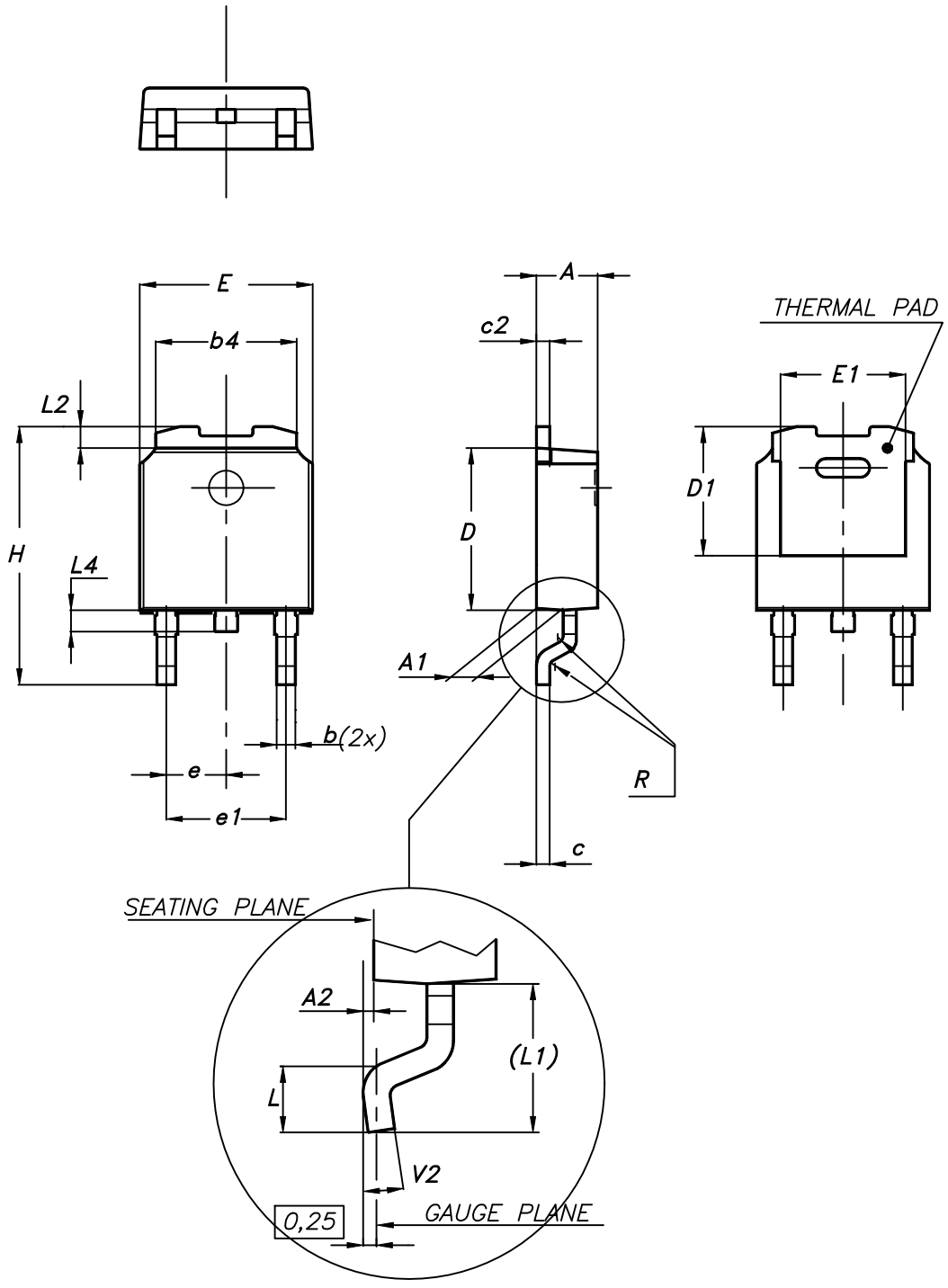
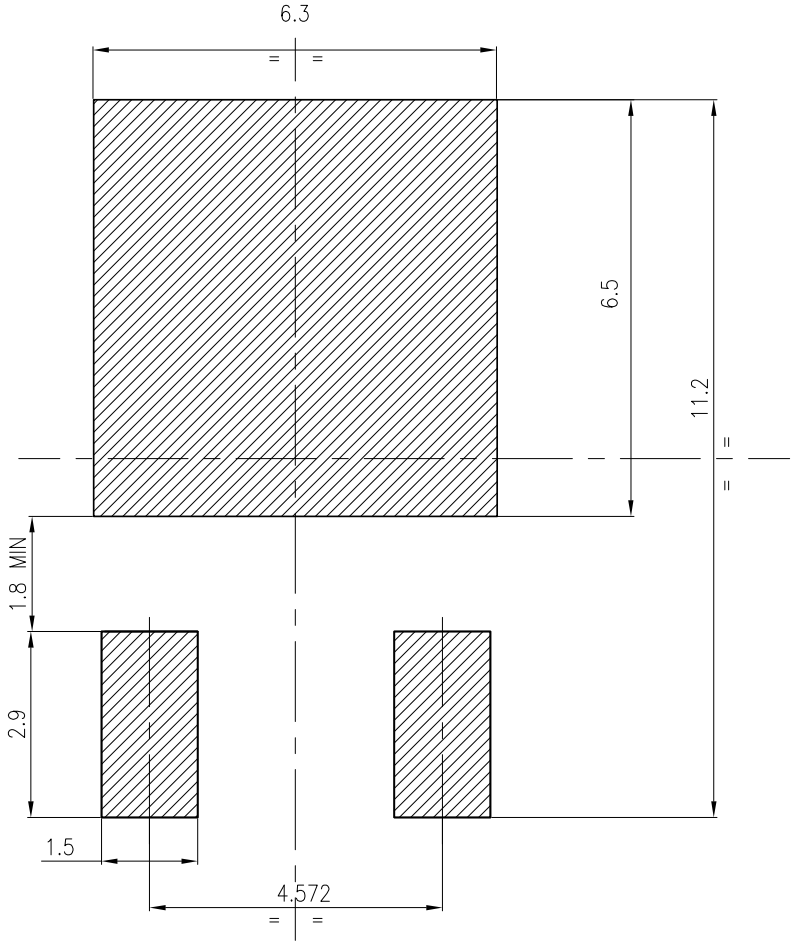


Table 7. **DPAK (TO-252) type A2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 20. **DPAK (TO-252) recommended footprint (dimensions are in mm)**



4.2 DPAK (TO-252) packing information

Figure 21. **DPAK (TO-252) tape outline**

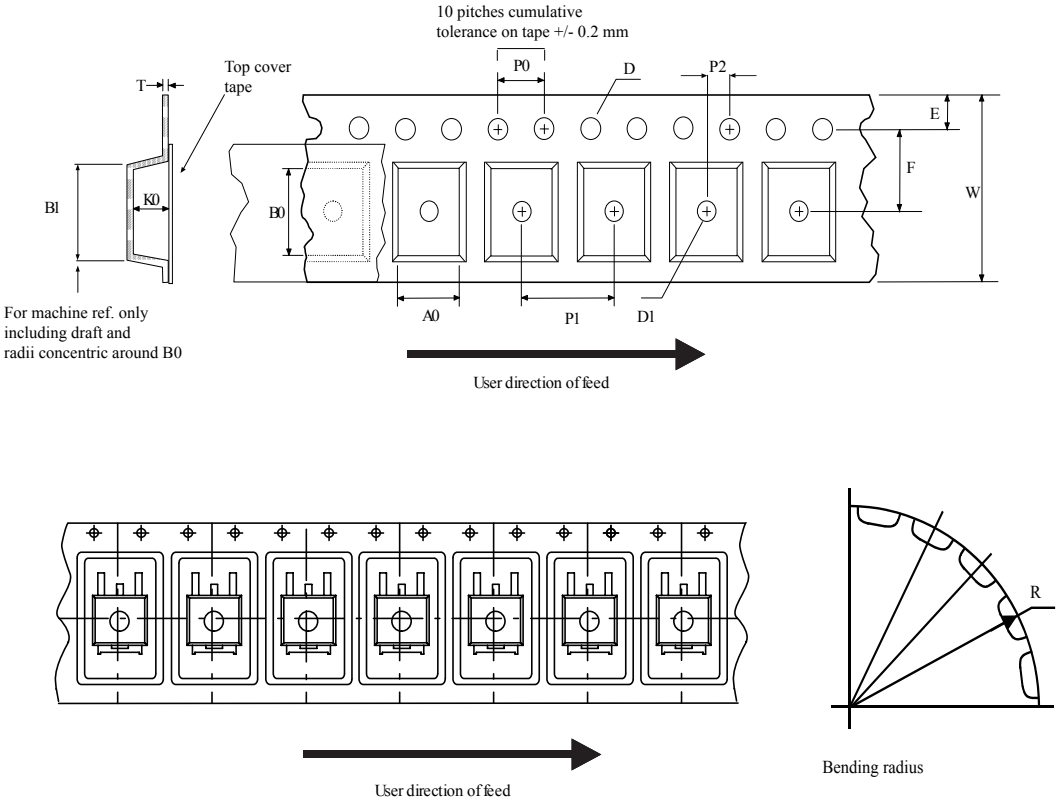


Figure 22. **DPAK (TO-252) reel outline**

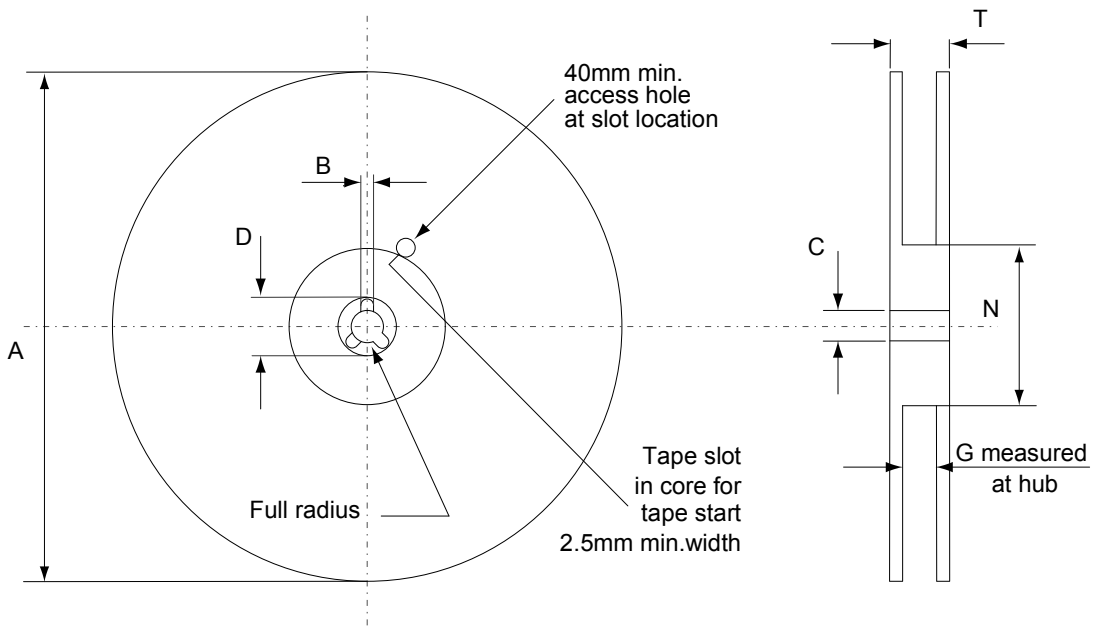


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Table 8. **DPAK (TO-252) tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Revision history

Table 9. **Document revision history**

Date	Version	Changes
17-Oct-2019	1	First release.

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